

MOS FIELD EFFECT TRANSISTOR

2SJ599

SWITCHING

P-CHANNEL POWER MOS FET

INDUSTRIAL USE

DESCRIPTION

The 2SJ599 is P-channel MOS Field Effect Transistor designed for solenoid, motor and lamp driver.

FEATURES

- Low on-state resistance:
 $R_{DS(on)1} = 75 \text{ m}\Omega \text{ MAX. (} V_{GS} = -10 \text{ V, } I_D = -10 \text{ A)}$
 $R_{DS(on)2} = 111 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.0 \text{ V, } I_D = -10 \text{ A)}$
- Low C_{iss} : $C_{iss} = 1300 \text{ pF TYP.}$
- Built-in gate protection diode
- TO-251/TO-252 package

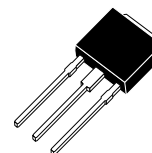
ORDERING INFORMATION

PART NUMBER	PACKAGE
2SJ599	TO-251
2SJ599-Z	TO-252

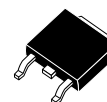
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	-60	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 20	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 50	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_T	35	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_T	1.0	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Single Avalanche Current ^{Note2}	I_{AS}	-20	A
Single Avalanche Energy ^{Note2}	E_{AS}	40	mJ

(TO-251)



(TO-252)



Notes 1. $PW \leq 10 \mu\text{s}$, Duty cycle $\leq 1\%$

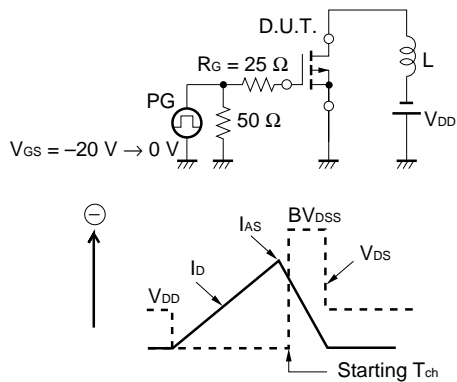
2. Starting $T_{ch} = 25^\circ\text{C}$, $R_G = 25 \Omega$, $V_{GS} = -20 \text{ V} \rightarrow 0 \text{ V}$

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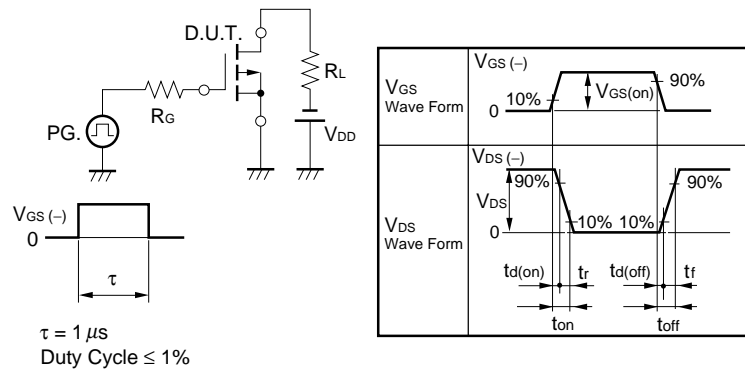
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -60 V, V _{GS} = 0 V			-10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1 mA	1.5	2.0	2.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = -10 V, I _D = -10 A	8	16		S
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = -10 V, I _D = -10 A		60	75	mΩ
	R _{DS(on)2}	V _{GS} = -4.0 V, I _D = -10 A		78	111	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz		1300		pF
Output Capacitance	C _{oss}			240		pF
Reverse Transfer Capacitance	C _{rss}			100		pF
Turn-on Delay Time	t _{d(on)}	I _D = -10 A, V _{GS(on)} = -10 V, V _{DD} = -30 V, R _G = 0 Ω		8		ns
Rise Time	t _r			9		ns
Turn-off Delay Time	t _{d(off)}			52		ns
Fall Time	t _f			16		ns
Total Gate Charge	Q _G	I _D = -20 A, V _{DD} = -48 V, V _{GS} = -10 V		26		nC
Gate to Source Charge	Q _{GS}			5		nC
Gate to Drain Charge	Q _{GD}			7		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = -20 A, V _{GS} = 0 V		1.0		V
Reverse Recovery Time	t _{rr}	I _F = -20 A, V _{GS} = 0 V		51		ns
Reverse Recovery Charge	Q _{rr}	di/dt = -100 A/μs		102		nC

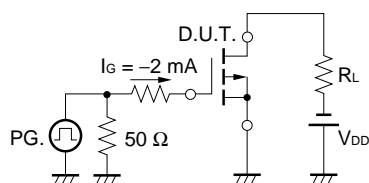
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

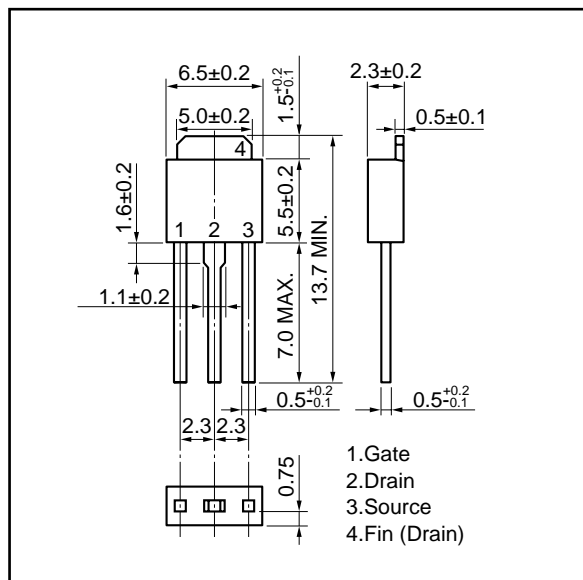


TEST CIRCUIT 3 GATE CHARGE

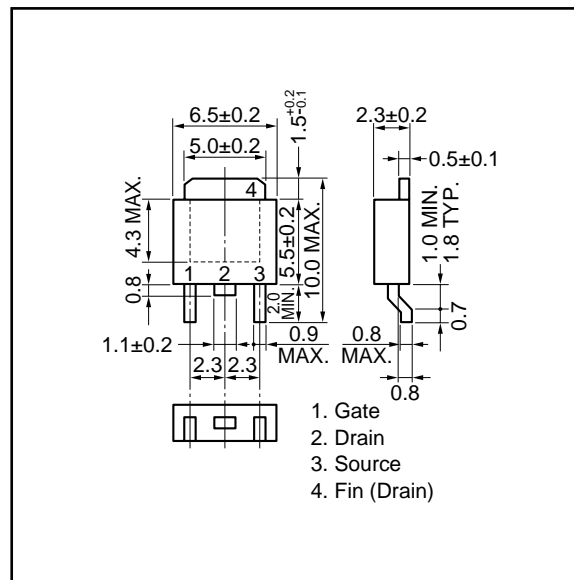


PACKAGE DRAWINGS (Unit : mm)

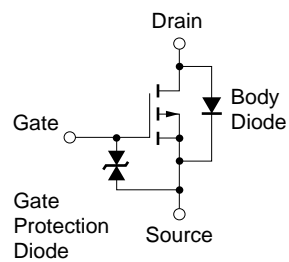
1) TO-251 (MP-3)



2) TO-252 (MP-3Z)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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